

Kwangeun Kim

List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	Environmentally and Electrically Stable Sol-Gel-Deposited SnO ₂ Thin-Film Transistors with Controlled Passivation Layer Diffusion Penetration Depth That Minimizes Mobility Degradation. ACS Applied Materials & Interfaces, 2022, 14, 10558-10565.	8.0	9
2	Enhanced Switching Reliability of Sol-Gel-Processed Y ₂ O ₃ RRAM Devices Based on Y ₂ O ₃ Surface Roughness-Induced Local Electric Field. Materials, 2022, 15, 1943.	2.9	8
3	Flexible Sol-Gel-Processed Y ₂ O ₃ RRAM Devices Obtained via UV/Ozone-Assisted Photochemical Annealing Process. Materials, 2022, 15, 1899.	2.9	8
4	Room-Temperature High-Detectivity Flexible Near-Infrared Photodetectors with Chalcogenide Silver Telluride Nanoparticles. ACS Omega, 2022, 7, 10262-10267.	3.5	4
5	Performance Optimization of Nitrogen Dioxide Gas Sensor Based on Pd-AlGa _N /Ga _N HEMTs by Gate Bias Modulation. Micromachines, 2021, 12, 400.	2.9	9
6	Extremely bias stress stable enhancement mode sol-gel-processed SnO ₂ thin-film transistors with Y ₂ O ₃ passivation layers. Applied Surface Science, 2021, 559, 149971.	6.1	20
7	Analysis on Trap States in p-Metal-Oxide-Semiconductor Capacitors with Ultraviolet/Ozone-Treated Ga _N Interfaces Through Frequency-Dispersion Capacitance Voltage Measurements. Electronic Materials Letters, 2020, 16, 140-145.	2.2	4
8	Improving Ni/GaN Schottky diode performance through interfacial passivation layer formed via ultraviolet/ozone treatment. Current Applied Physics, 2020, 20, 293-297.	2.4	4
9	Polarization-Charge Inversion at Al ₂ O ₃ /Ga _N Interfaces through Post-Deposition Annealing. Electronics (Switzerland), 2020, 9, 1068.	3.1	4
10	AlGa _N /Ga _N Schottky-Gate HEMTs With UV/O ₃ -Treated Gate Interface. IEEE Electron Device Letters, 2020, 41, 1488-1491.	3.9	13
11	Effect of Mg Doping on the Electrical Performance of a Sol-Gel-Processed SnO ₂ Thin-Film Transistor. Electronics (Switzerland), 2020, 9, 523.	3.1	16
12	Metal-Al ₂ O ₃ -Ga _N capacitors with an ultraviolet/ozone plasma-treated interface. Japanese Journal of Applied Physics, 2020, 59, 030908.	1.5	8
13	Improved conduction in Ga _N Schottky junctions with HfO ₂ passivation layers through post-deposition annealing. Japanese Journal of Applied Physics, 2020, 59, 030902.	1.5	2
14	Enhancement Mode Flexible SnO ₂ Thin Film Transistors Via a UV/Ozone-Assisted Sol-Gel Approach. IEEE Access, 2020, 8, 123013-123018.	4.2	10
15	Investigation in the Ga ₂ O ₃ passivation layer formed as Ga _N Schottky barrier through UV/O ₃ treatment. Results in Physics, 2020, 16, 102964.	4.1	2
16	Sol-Gel Processed Yttrium-Doped SnO ₂ Thin Film Transistors. Electronics (Switzerland), 2020, 9, 254.	3.1	29
17	Effect of Annealing Ambient on SnO ₂ Thin Film Transistors Fabricated via An Ethanol-based Sol-gel Route. Electronics (Switzerland), 2019, 8, 955.	3.1	15
18	Effect of Annealing Environment on the Performance of Sol-Gel-Processed ZrO ₂ RRAM. Electronics (Switzerland), 2019, 8, 947.	3.1	18

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19	Reduction of Leakage Current in GaN Schottky Diodes Through Ultraviolet/Ozone Plasma Treatment. IEEE Electron Device Letters, 2019, 40, 1796-1799.	3.9	18
20	229-nm UV LEDs on aluminum nitride single crystal substrates using p-type silicon for increased hole injection. Applied Physics Letters, 2018, 112, .	3.3	52
21	Photolithography-Based Nanopatterning Using Re-entrant Photoresist Profile. ACS Applied Materials & Interfaces, 2018, 10, 8117-8123.	8.0	8
22	Efficiency enhancement of InGaN/GaN blue light-emitting diodes with top surface deposition of AlN/Al ₂ O ₃ . Nano Energy, 2018, 43, 259-269.	16.0	31
23	226-nm AlGaN/AlN UV LEDs using p-type Si for hole injection and UV reflection. Applied Physics Letters, 2018, 113, .	3.3	59
24	Band-Bending of Ga-Polar GaN Interfaced with Al ₂ O ₃ through Ultraviolet/Ozone Treatment. ACS Applied Materials & Interfaces, 2017, 9, 17576-17585.	8.0	25
25	Transferrable single crystalline 4H-SiC nanomembranes. Journal of Materials Chemistry C, 2017, 5, 264-268.	5.5	30